

光鋳科技股份有限公司

Epileds Technologies, Inc.

Product specification of 24x24 mil blue LED chip.

1. Scope:

This specification applies to InGaN/GaN 24 x 24 mil blue LED chip, EP-B2424B-A2、EP-B2424B-A3、EP-B2424B-A4。

2. Materials :

2.1 P-contact : Conductive Layer。

2.2 P-pad : Au。

2.3 N-pad : Au。

2.4 Backside Metal:

EP- B2424B -A2 : Reflective Layer (Al)

EP- B2424B -A3 : Reflective Layer (Al) with Au

EP- B2424B -A4 : Reflective Layer (Al) with AuSn

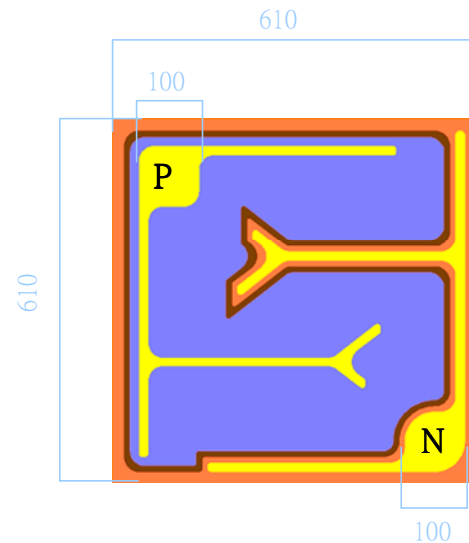
3. Dimensions :

3.1 Chip size : $610 \pm 10 \mu\text{m} \times 610 \pm 10 \mu\text{m}$ 。

3.2 P-pad : $\phi 100 \pm 10 \mu\text{m}$, thickness $1.2 \pm 0.1 \mu\text{m}$ 。

3.3 N-pad : $\phi 100 \pm 10 \mu\text{m}$, thickness $1.2 \pm 0.1 \mu\text{m}$ 。

3.4 Chip thickness : $150 \mu\text{m} \pm 10 \mu\text{m}$ 。



4. Electro-optical characteristics and specification: (Tc=25°C)

4.1 Electro-optical characteristics

Test parameter	Condition	Min	Typ	Max	Unit
Dominant wavelength(Wd)	150mA	445	-	475	nm
Radiant intensity(I)	150mA	40	-	135	mW/sr
Forward voltage(Vf4)	10uA	1.9	-	2.5	V
Forward voltage(Vf1)	150mA	2.8	-	3.8	V
Reverse current (Ir)	-5V	0	-	2	uA

4.2 Electro-optical specification(Bin table) :

Wd		I		Vf1	Vf4	Ir
Bin	nm	Bin	mW/sr	(V)	(V)	(uA)
PS	445~447.5	81	40~45	2.8~3.8	1.9~2.5	0~2
PT	447.5~450	82	45~50			
BA	450~452.5	83	50~60			
BB	452.5~455	45	60~70			
BC	455~457.5	46	70~80			
BD	457.5~460	47	80~90			
BE	460~462.5	84	90~100			
BF	462.5~465	85	100~110			
BG	465~467.5	86	110~120			
BH	467.5~470	87	120~135			
BI	470~472.5					
BJ	472.5~475					

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* The detail technical and reliability datasheet are also available for your reference, please be free to contact us.